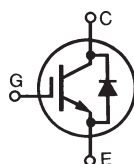


Medium speed low V<sub>sat</sub> PT  
IGBT for 5-40kHz switching

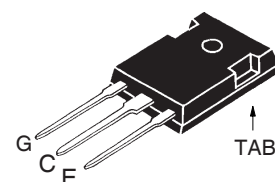


$$V_{CES} = 600V$$

$$I_{C110} = 36A$$

$$V_{CE(sat)} \leq 1.8V$$

Symbol	Test Conditions	Maximum	Ratings
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	600	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C110}$	$T_C = 110^\circ C$	36	A
$I_{F110}$	$T_C = 110^\circ C$	10	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	200	A
<b>SSOA</b>	$V_{GE} = 15V$ , $T_J = 125^\circ C$ , $R_G = 5\Omega$	$I_{CM} = 80$	A
<b>(RBSOA)</b>	Clamped inductive load @ $V_{CE} \leq 600V$		
$P_C$	$T_C = 25^\circ C$	250	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
$T_L$	Maximum lead temperature for soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062 in.) from case for 10s	260	$^\circ C$
<b>Weight</b>		6	g

**TO-247 AD (IXGH)**


G = Gate      C = Collector  
E = Emitter    TAB = Collector

**Features**

- Optimized for low conduction and switching losses
- Square RBSOA
- Anti-parallel ultra fast diode
- International standard package

**Advantages**

- High power density
- Low gate drive requirement

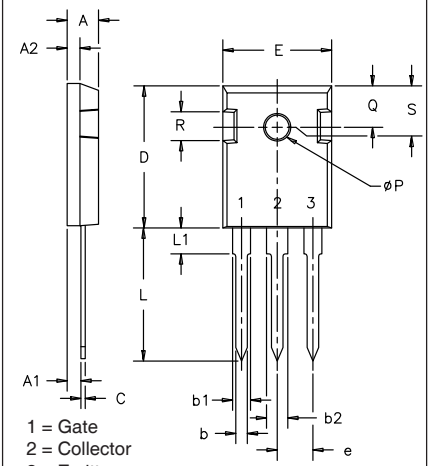
**Applications**

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ( $T_J = 25^\circ C$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		V
$I_{CES}$	$V_{CE} = V_{CES}$ $V_{GE} = 0V$ $T_J = 125^\circ C$			75 $\mu A$ 500 $\mu A$
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 30A$ , $V_{GE} = 15V$ , Note 1	1.5	1.8	V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 30\text{A}, V_{CE} = 10\text{V}$ , Note 1	28	42	S
$C_{ies}$ $C_{oes}$ $C_{res}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		2280	pF
			120	pF
			32	pF
$Q_g$ $Q_{ge}$ $Q_{gc}$	$I_C = 30\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		80	nC
			12	nC
			36	nC
$t_{d(on)}$ $t_{ri}$ $E_{on}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 5\Omega$		19	ns
			24	ns
			0.54	mJ
			125	200 ns
			100	160 ns
			0.80	1.5 mJ
$t_{d(on)}$ $t_{ri}$ $E_{on}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 5\Omega$		19	ns
			26	ns
			0.90	mJ
			180	ns
			170	ns
			1.50	mJ
$R_{thJC}$ $R_{thCK}$		0.21	0.50 °C/W °C/W	

TO-247 (IXGH) AD Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.7	5.3
A1	.087	.102	2.2	2.54
A2	.059	.098	2.2	2.6
b	.040	.055	1.0	1.4
b1	.065	.084	1.65	2.13
b2	.113	.123	2.87	3.12
C	.016	.031	.4	.8
D	.819	.845	20.80	21.46
E	.610	.640	15.75	16.26
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1		.177		4.50
øP	.140	.144	3.55	3.65
Q	.212	.244	5.4	6.2
R	.170	.216	4.32	5.49
S	.242 BSC		6.15 BSC	

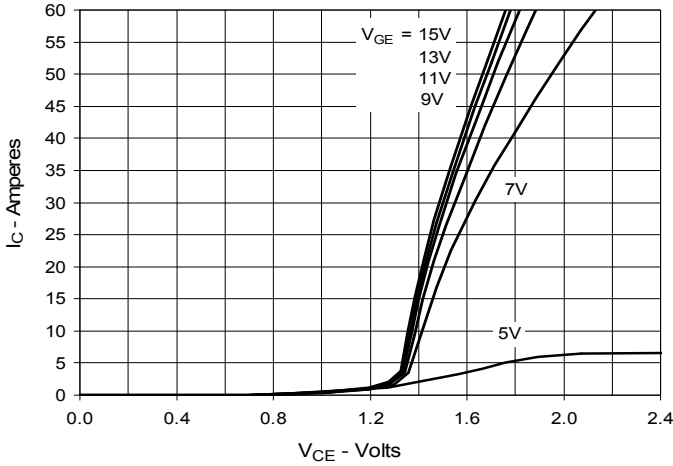
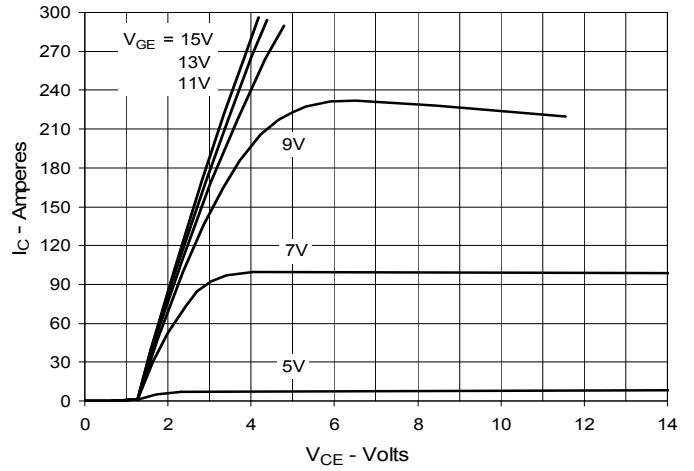
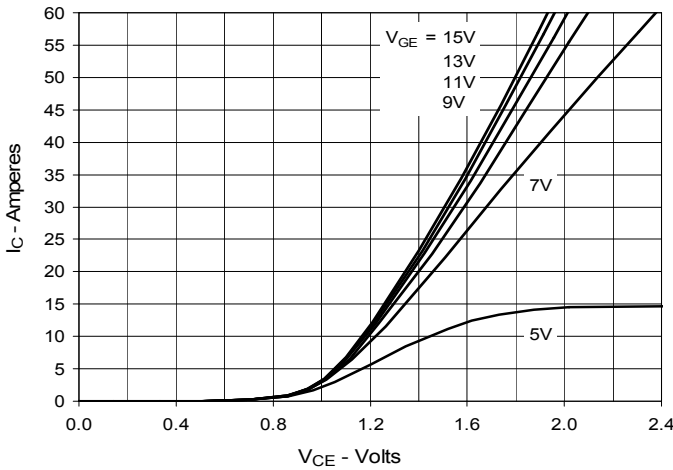
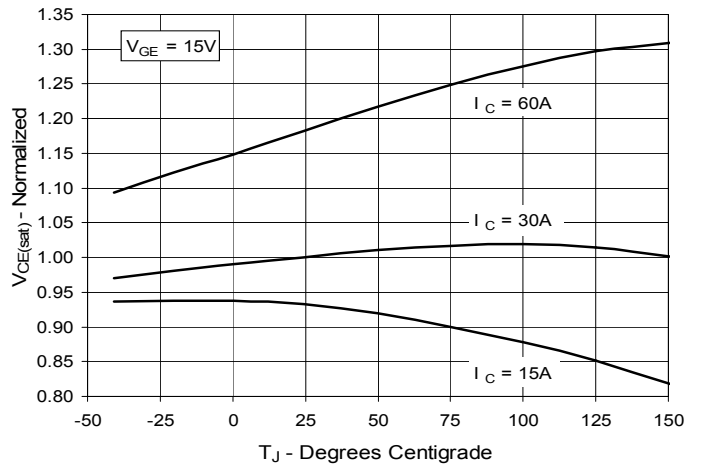
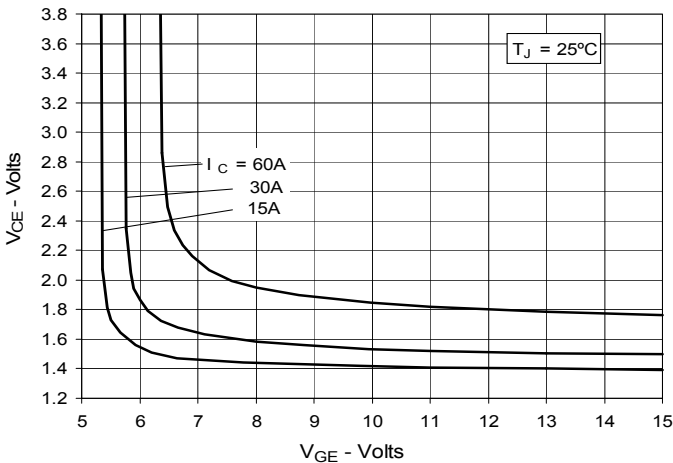
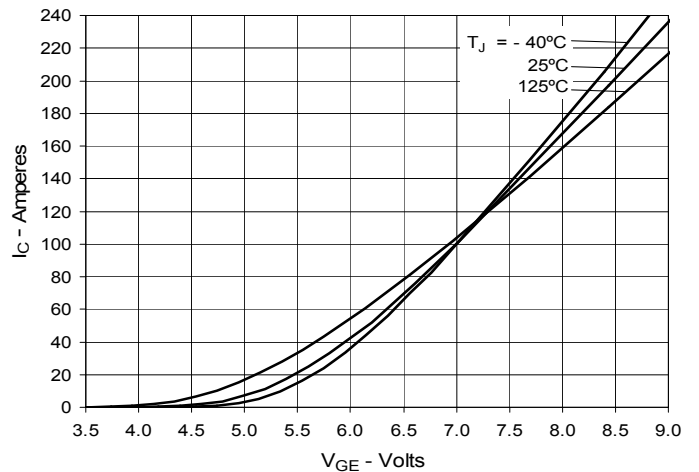
**Reverse Diode (FRED)**

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_F$	$I_F = 10\text{A}, V_{GE} = 0\text{V}$ , Note 1 $T_J = 150^\circ\text{C}$		1.7	3.0 V V
$t_{rr}$ $I_{RM}$	$I_F = 10\text{A}, -di_F/dt = 200\text{A}/\mu\text{s}$ $V_R = 300\text{V}$ $T_J = 100^\circ\text{C}$ $T_J = 25^\circ\text{C}$ $T_J = 100^\circ\text{C}$		60	ns
				3 4
$R_{thJC}$				2.5 °C/W

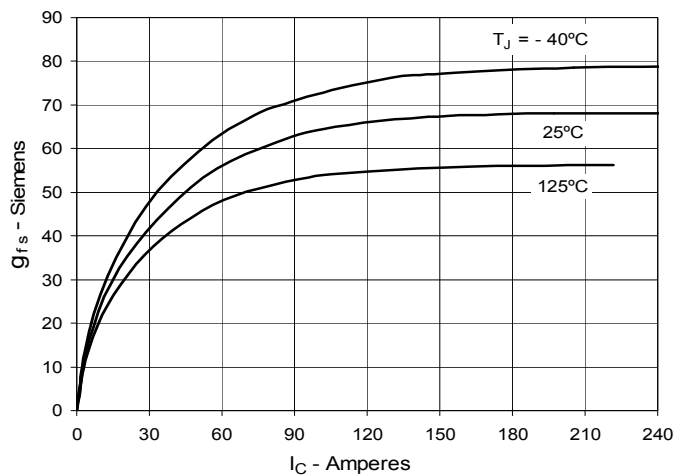
Notes: 1. Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

IXYS reserves the right to change limits, test conditions, and dimensions.

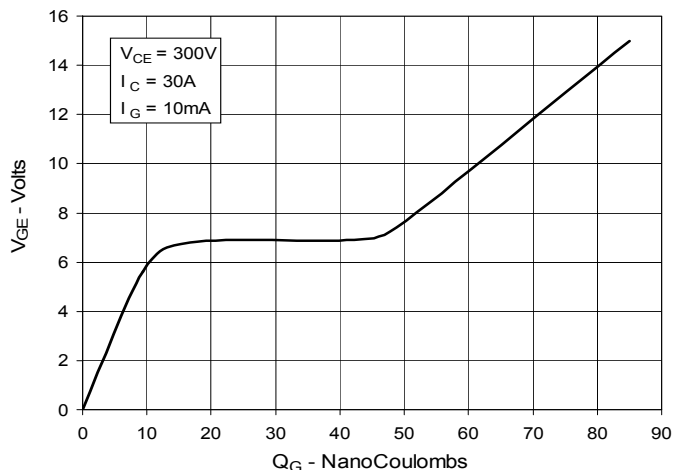
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @ 25°C**

**Fig. 2. Extended Output Characteristics @ 25°C**

**Fig. 3. Output Characteristics @ 125°C**

**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**

**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**

**Fig. 6. Input Admittance**


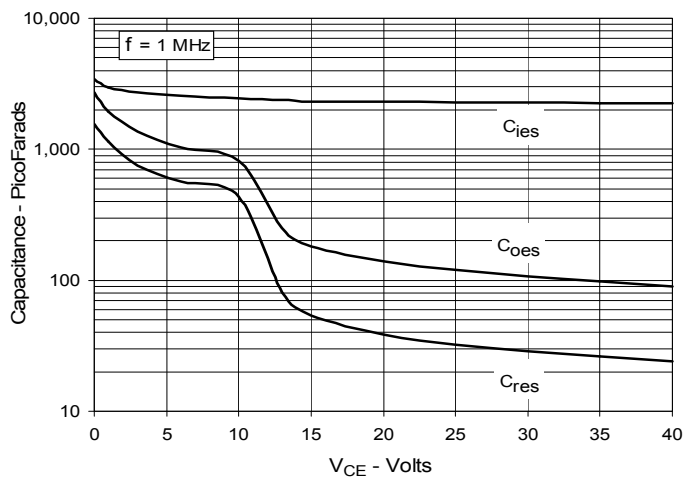
**Fig. 7. Transconductance**



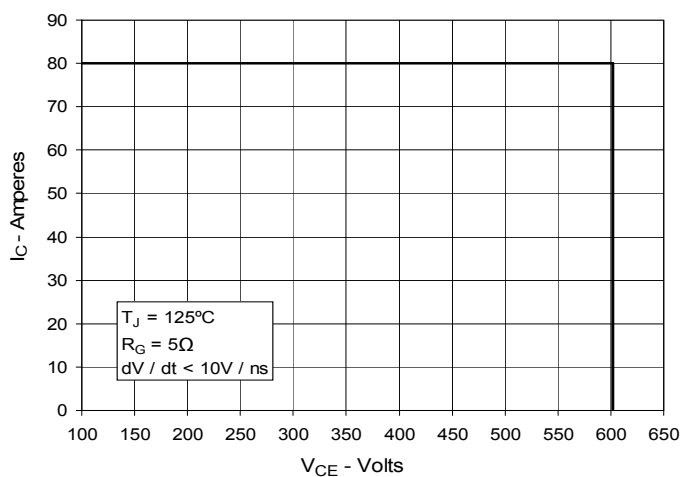
**Fig. 8. Gate Charge**



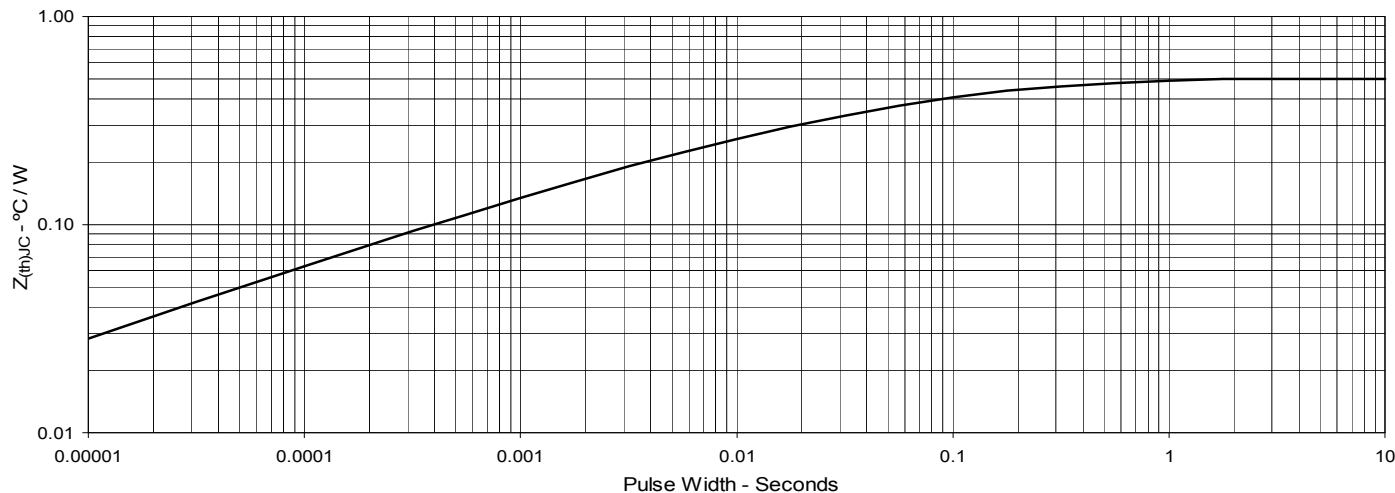
**Fig. 9. Capacitance**



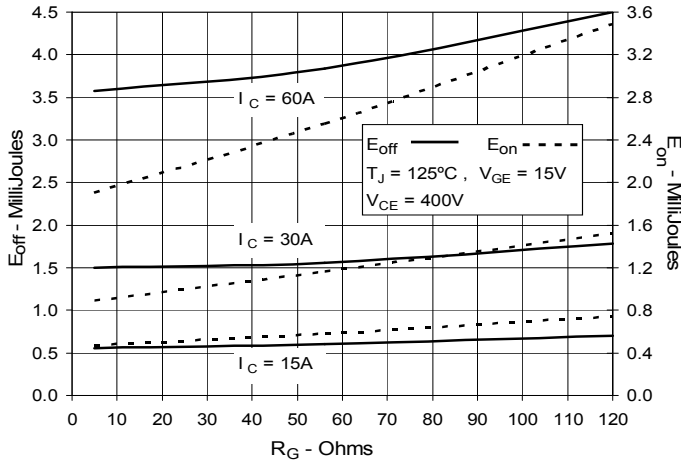
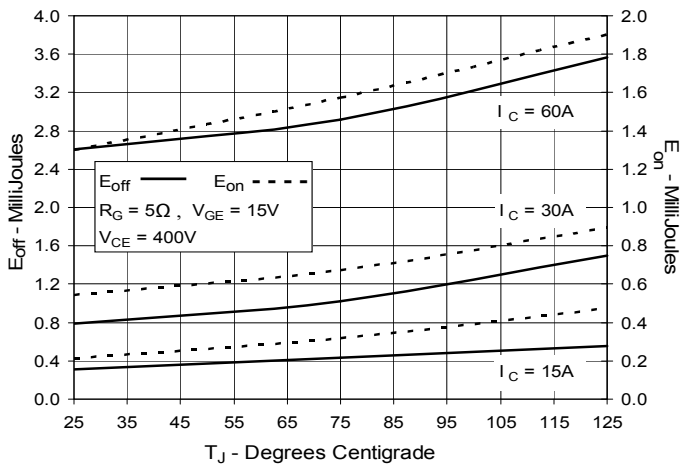
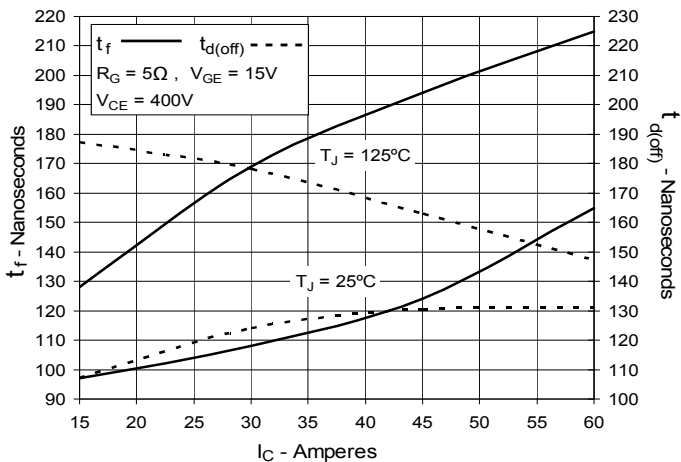
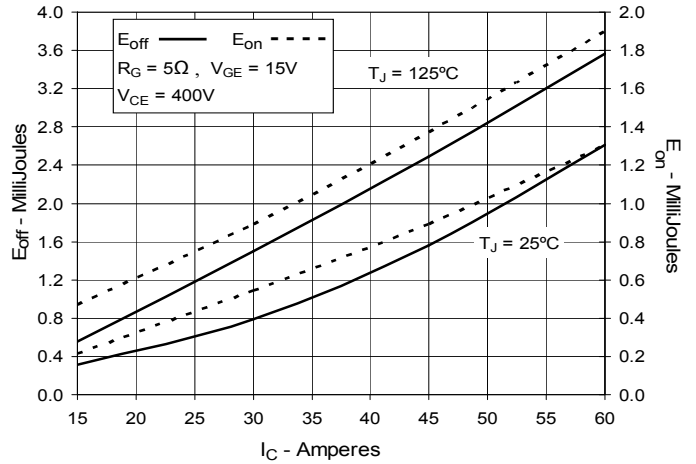
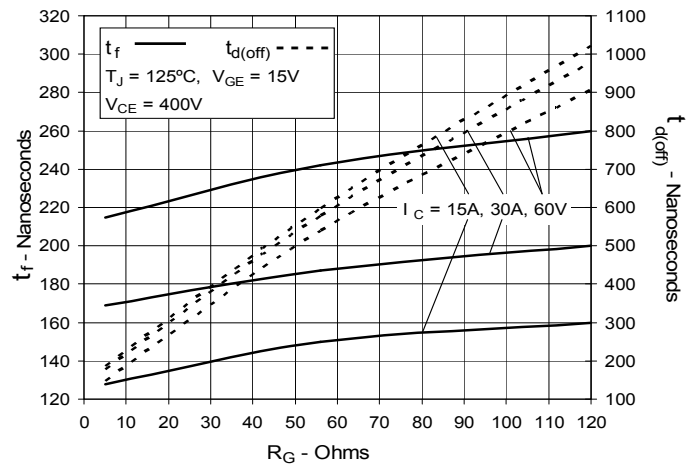
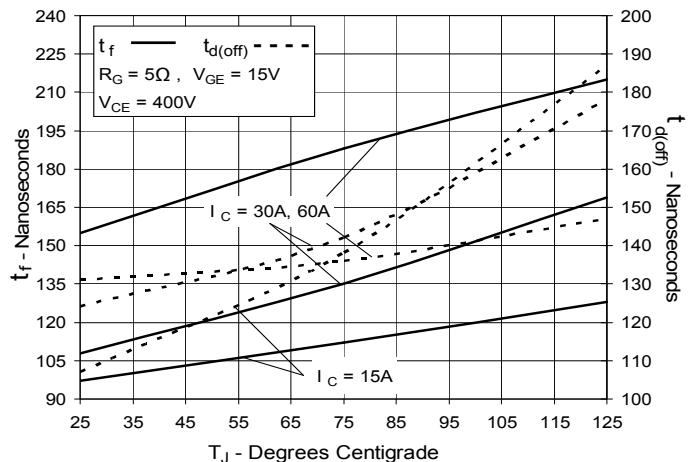
**Fig. 10. Reverse-Bias Safe Operating Area**

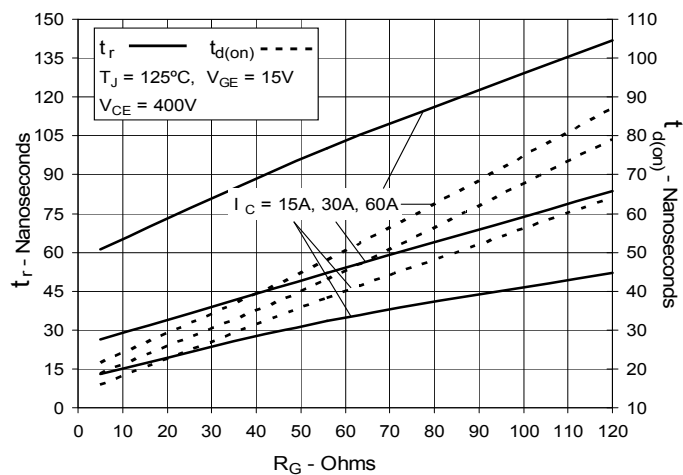
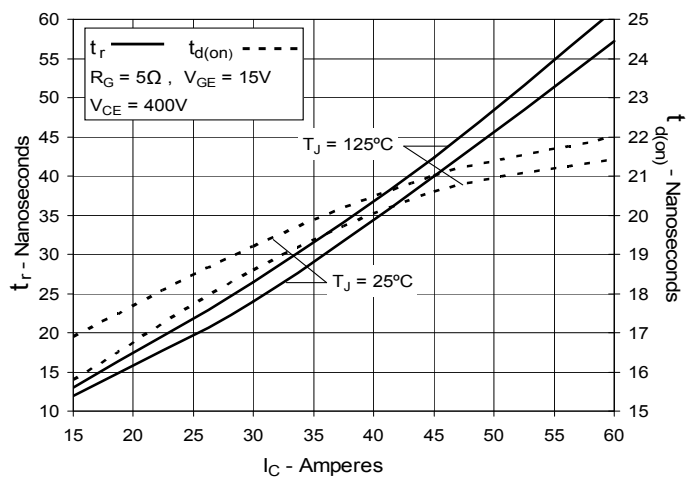
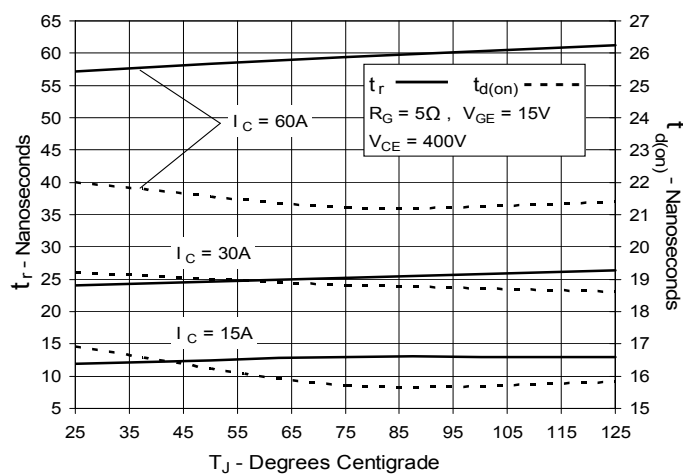


**Fig. 11. Maximum Transient Thermal Impedance**



IXYS reserves the right to change limits, test conditions, and dimensions.

**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**

**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**

**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**

**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**

**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**

**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**


**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**

**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**

**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**


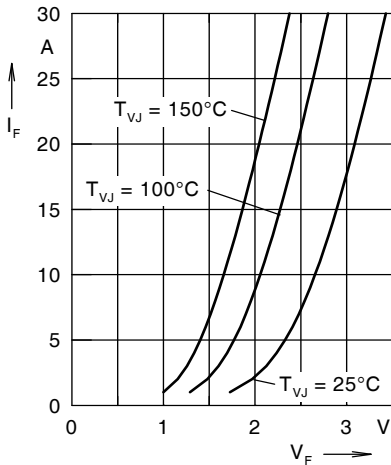


Fig. 21. Forward current  $I_F$  versus  $V_F$

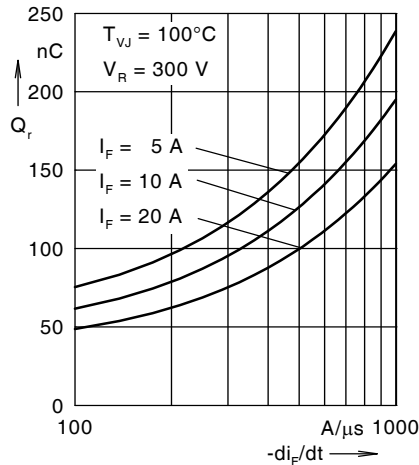


Fig. 22. Reverse recovery charge  $Q_r$

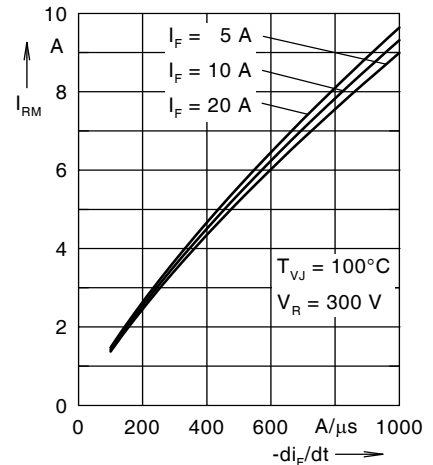


Fig. 23. Peak reverse current  $I_{RM}$

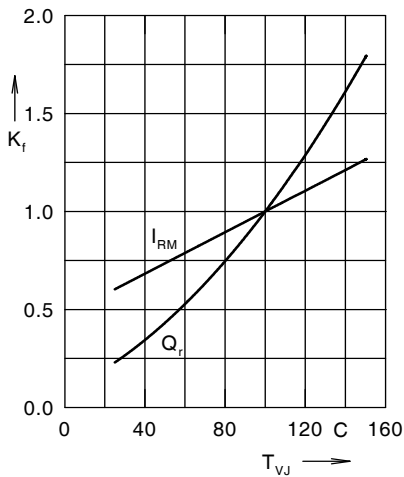


Fig. 24. Dynamic parameters  $Q_r$ ,  $I_{RM}$

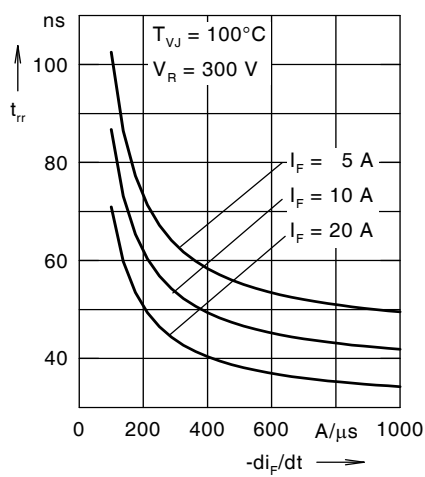


Fig. 25. Recovery time  $t_{rr}$  versus  $-di_F/dt$

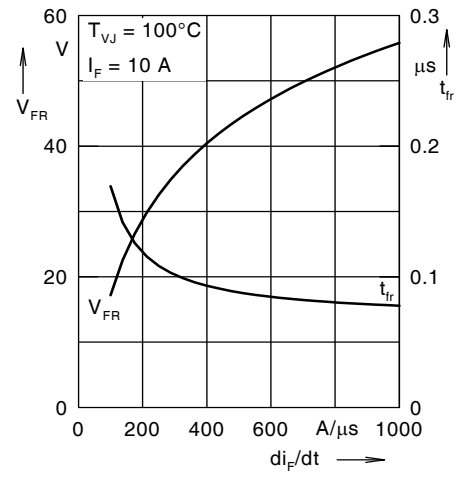


Fig. 26. Peak forward voltage  $V_{FR}$  and  $t_{rr}$

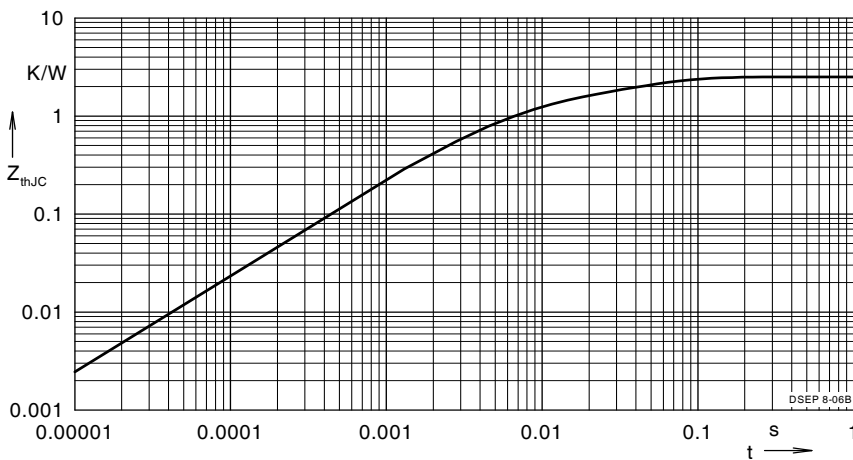


Fig. 27. Transient thermal resistance junction-to-case

NOTE: Fig. 2 to Fig. 6 shows typical values

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	1.449	0.0052
2	0.5578	0.0003